PIN Diode Qualification

Devices Tested QA Procedure Outline Results

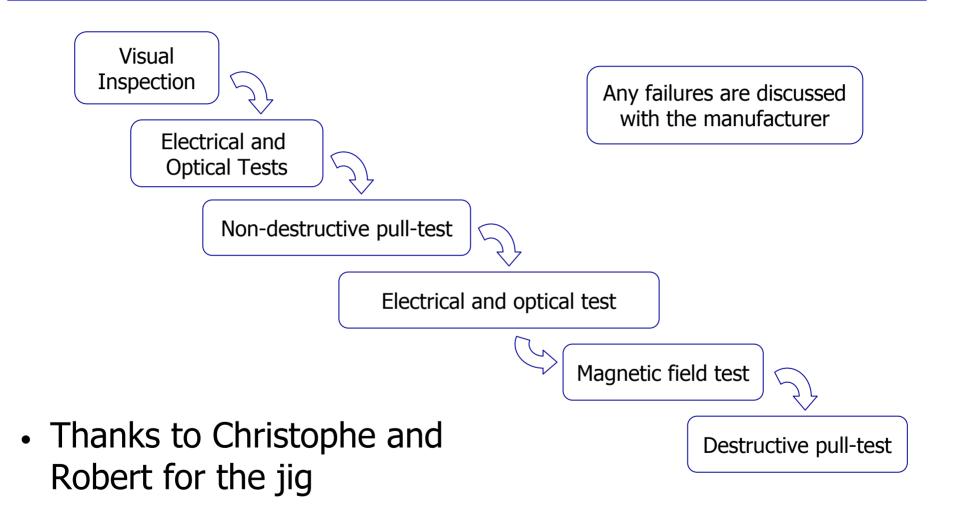
giulia papotti

Introduction

- 190 diodes delivered from Fermionics
 - 90 diodes for AVT
 - 100 diodes for pre-production qualification
 - come from 3 different wafers:
 - Serial number 1-33, wafer W770J-D
 - Serial number 34-66, wafer W517I-M
 - Serial number 67-100, wafer W520I-R
- 50 re-qualification diodes from wafer W517I-M
 - Serial number 191-241, without 226



Qualification procedure





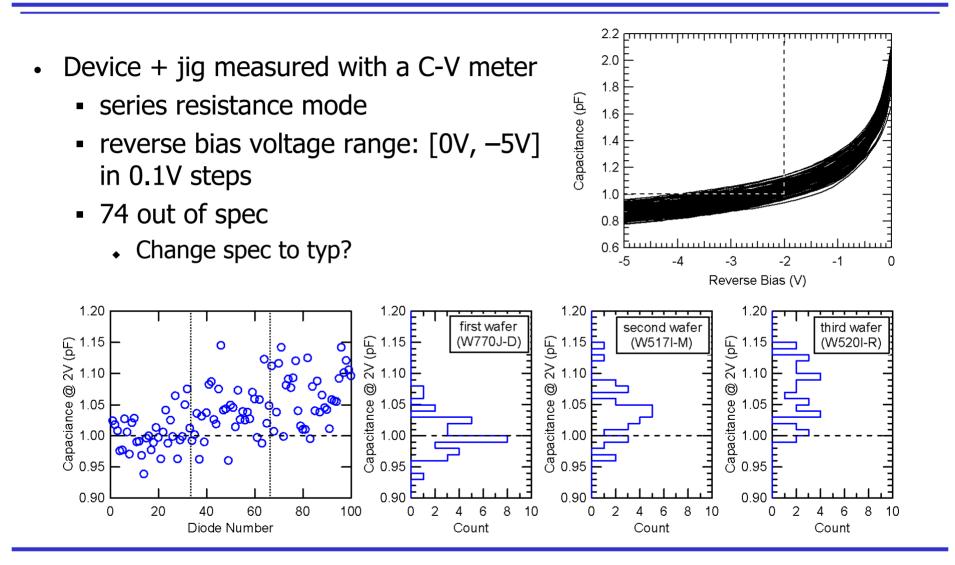
Visual Inspection

- Inspection of the pigtail:
 - Measured lengths
 - Found light scratches on the fibres
- Inspection of the dimensions of the package
- Scan codes properly attached

• Thanks to Etam and Margherita



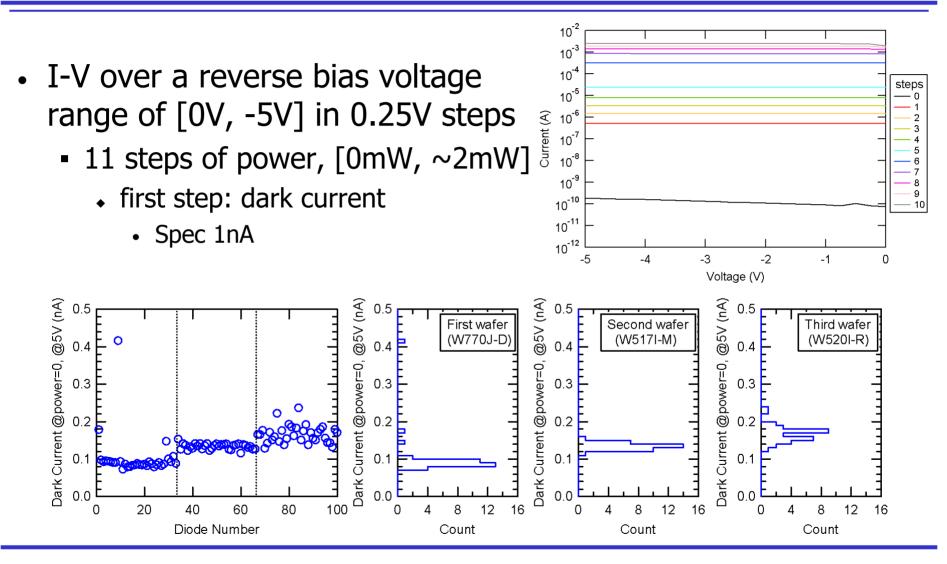
Capacitance





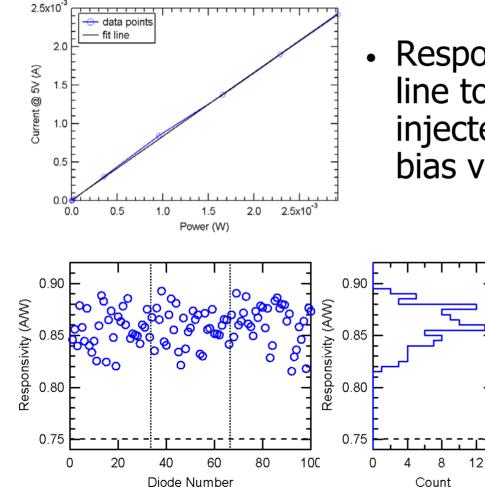
giulia papotti

Dark Current & Responsivity - 1





Dark Current & Responsivity - 2



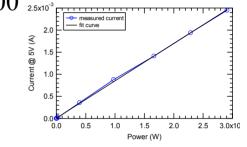
Responsivity: slope of the fit
line to photocurrent versus
injected optical power at -5
bias voltage

- Spec 0.75A/W
- No appreciable difference between wafers

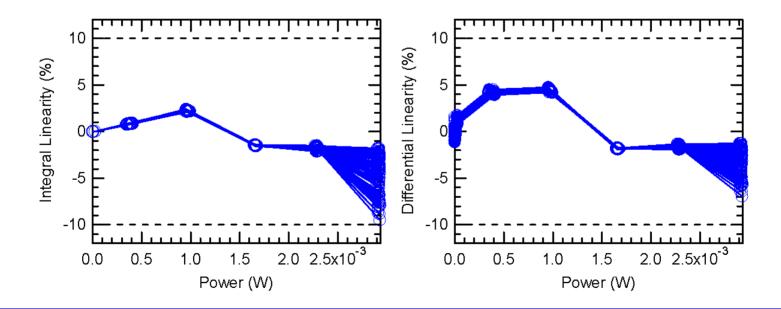


Dark Current & Responsivity - 3

- Differential Linearity: Diff.Lin (%) = $\frac{\text{Curr}@5 \text{fitline}}{\text{Curr}@5} \cdot 100_{2.5 \times 10^{3}}$
- Integral Linearity: Int.Lin (%) = $\frac{\text{Curr}@5 \text{fitline}}{\text{resp} \cdot 2\text{mW}} \cdot 100$



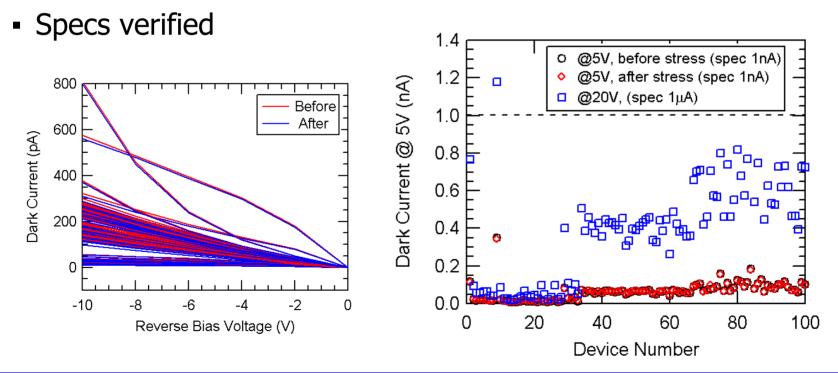
No spec to meet





-20V Stress - Maximum Reverse Bias Voltage

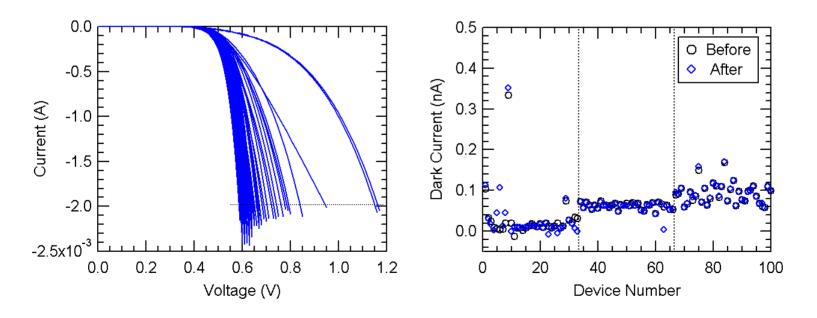
- Dark current in the range [0V, -10V] in 2V steps, before and after biasing the device at -20V for 5 seconds
 - No device has been damaged by the biasing at -20V





Maximum Forward Current

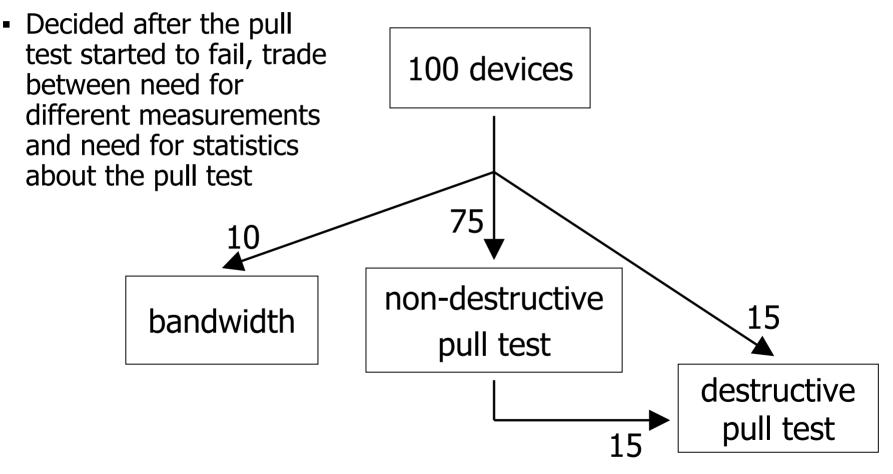
- Diode forward-biased with the voltage being increased from 0V in steps of 0.01V until the forward current exceeds 2mA
- Dark current at -5V measured before and after the sweep
 - Spec is 1nA





Subsequent Measurements

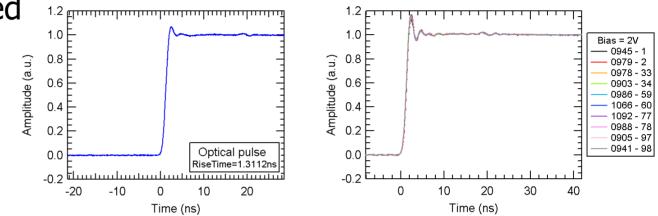
• 100 devices tested then according to different measurements

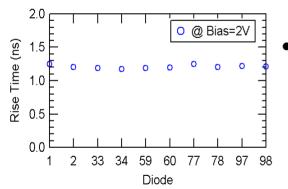




Bandwidth

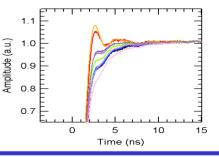
 Diode connected to scope as optical head, with -2V bias, and fast pulse train applied





Diode should not increase the rise time (10%-90%) of the pulse more than 3ns

Note: the behaviours are quite different when the bias is 0V: some diodes are slower





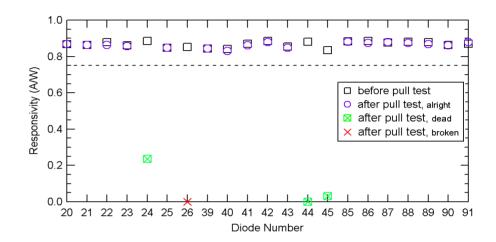
Non-Destructive Pull Test - 1

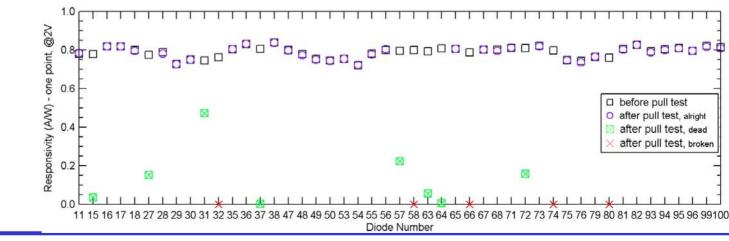
- Need to compare performance before and after pulling
- Early failures led to decide to test more devices
 - Three different test set-ups had to be used
 - 1st test: comparison of responsivity for 21 diodes
 - 2nd test: 2 lasers used, no comparison available
 - on 7 devices, which did not break
 - 3rd test: 1-point measurement for 47 devices



Non-Destructive Pull Test -2

- Two different kinds of failure:
 - Diode detached from pigtail (*broken*)
 - Diode still attached but with low responsivity (*dead*)
- 17 failures in total (23%)
 - 11 dead
 - 6 broken

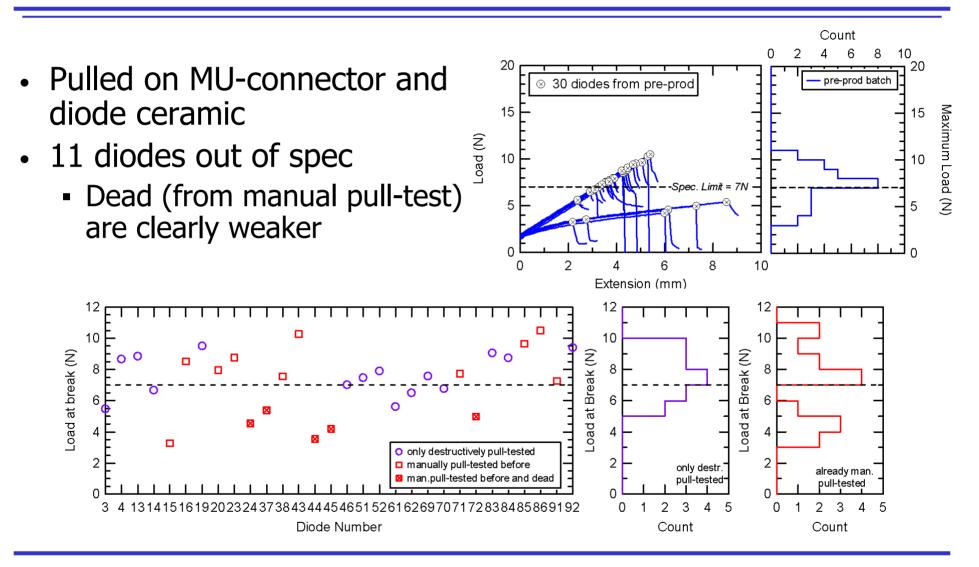






giulia papotti

Destructive pull-test

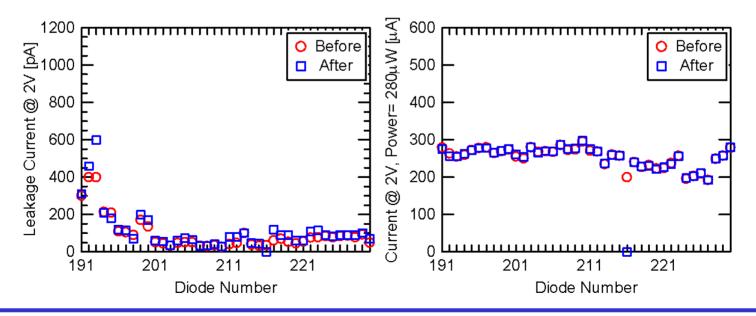




- 50 devices delivered after failure of pre-production
 - 40 non-destructively pull-tested
 - 30 (20 from 40 + 10 new ones) destr. pull-tested
- Visual inspection on 40 devices:
 - 2 cathodes 2.5mm long instead of 4mm
 - No bad scratches on fibre
 - Antistatic aluminum bends the pins

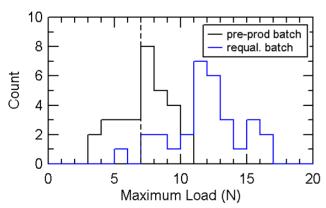


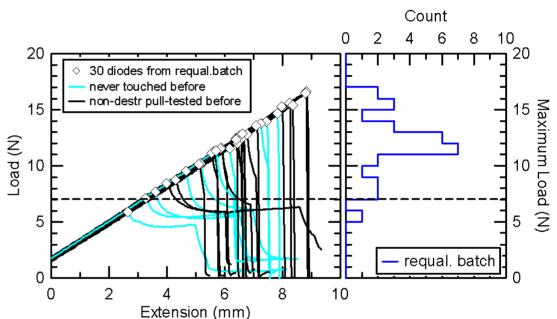
- Leakage current and photocurrent measured before and after the manual pull-test
 - Still not perfect, but very good improvement:
 - No *dead* ones, but 1 broke





- 30 diodes destroyed
 - No difference between new ones and pulltested before ones
 - One broke on the MU side

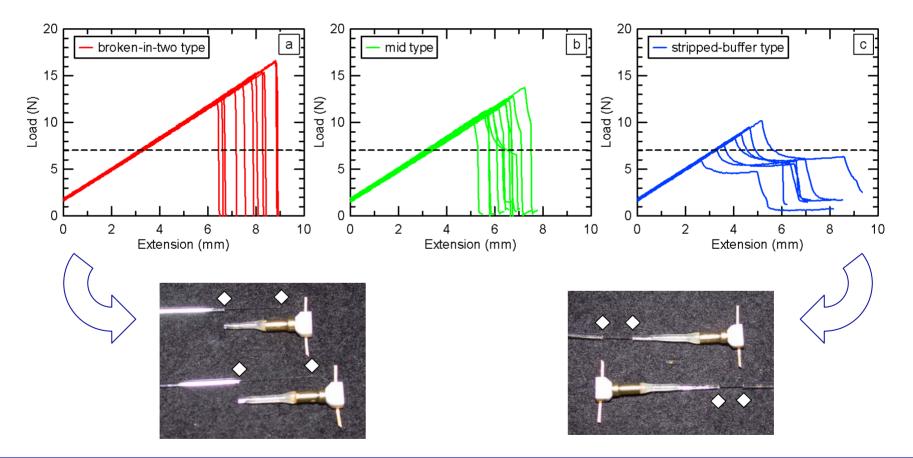




Joint much stronger than before



Two different types of breakage observed





Summary

- As always, nothing is perfect at the first attempt
 - Some doubts about the visual inspection
 - Capacitance not perfectly targeted
 - Diode-pigtail joint first found too weak
 - More glue solved the problem almost completely
 - Karl and Francois have the last word, but I think the diodes are **qualified**

